CHENMKO ENTERPRISE CO.,LTD

CH761UGP

Halogens free devices

SURFACE MOUNT
SCHOTTKY BARRIER DIODE
VOLTAGE 12 Volts CURRENT 0.1 Ampere

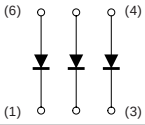
APPLICATION
* Low voltage high speed switching application

FEATURE
* Small surface mounting type. (SC-88/SOT-363)
* Low VF and low IR
* Three diodes in parallel installation
* Power dissipation is 200mW
* Maximum peak forward current is 200mA

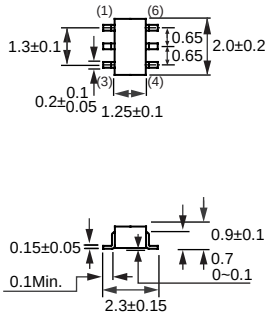
CONSTRUCTION
* Silicon epitaxial planar

MARKING
* JB

CIRCUIT



SC-88/SOT-363



Dimensions in millimeters

SC-88/SOT-363

MAXIMUM RATINGES (At T_A = 25°C unless otherwise noted)

RATINGS	SYMBOL	CH761UGP	UNITS
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	12	Volts
Maximum RMS Voltage	V_{RMS}	8	Volts
Maximum DC Blocking Voltage	V_{DC}	12	Volts
Maximum Average Forward Rectified Current	I_O	0.1	Amps
Peak Forward Surge Current at 8.3 mSec single half sine-wave	I_{FSM}	1.0	Amps
Typical Junction Capacitance between Terminal (Note 1)	C_J	30	pF
Operating Temperature Range	T_J	-40 to +125	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (At T_A = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CH761UGP			UNITS
		MIN.	TYP.	MAX.	
Maximum Instantaneous Forward Voltage at I_F= 1mA	V_F	-	0.16	-	Volts
I_F= 5mA		-	0.20	0.28	
I_F= 100mA		-	0.32	0.50	
Maximum Average Reverse Current at V_R= 20V	I_R	-	-	20	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0 volts.
2. ESD sensitive product handling required.

2007

RATING CHARACTERISTIC CURVES (CH761UGP)

FIG. 1 FORWARD CHARACTERISTICS

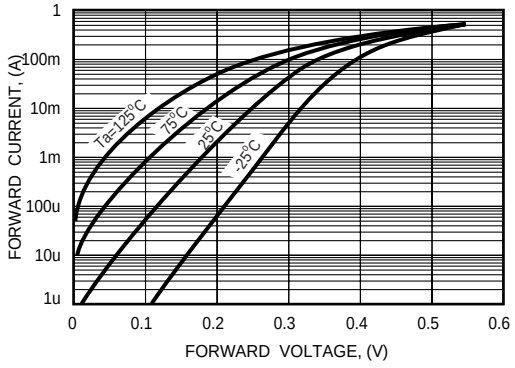


FIG. 2 - REVERSE CHARACTERISTICS

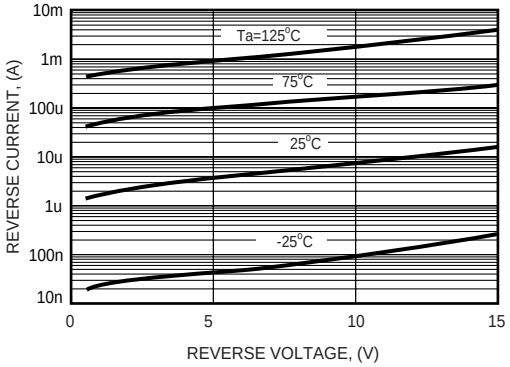


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

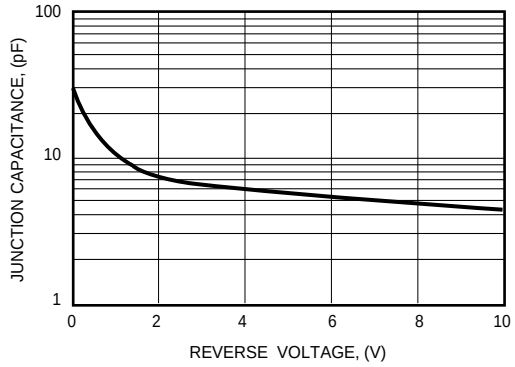


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE